



P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
	0.115 at V _{GS} = - 4.5 V	- 2.9		
- 20	0.155 at V _{GS} = - 2.5 V	- 2.4		
	0.220 at V _{GS} = - 1.8 V	- 2.0		

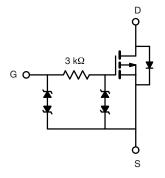
FEATURES

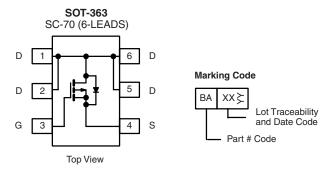
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET: 1.8 V Rated
- ESD Protected: 3000 V
- Thermally Enhanced SC-70 Package
- Compliant to RoHS Directive 2002/95/EC



APPLICATIONS

- Load Switching
- PA Switch
- · Level Switch





Ordering Information: Si1413EDH-T1-E3 (Lead (Pb)-free)

Si1413EDH-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS	$\Gamma_A = 25 ^{\circ}\text{C}$, unles	ss otherwise r	noted		
Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 20		V
Gate-Source Voltage		V _{GS}	± 12		
Continuous Dunis Comment /T. 150 90\d	T _A = 25 °C	- I _D	- 2.9	- 2.3	٨
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 85 °C		- 2.0	- 1.6	
Pulsed Drain Current		I _{DM}	- 8		Α
Continuous Diode Current (Diode Conduction) ^a		I _S	- 1.4 - 0.9		
Maximum Power Dissipation ^a	T _A = 25 °C	- P _D	1.56	1.0	w
	T _A = 85 °C		0.81	0.52	
Operating Junction and Storage Temperature Range		T _J , T _{stq}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	t ≤ 5 s	- R _{thJA}	60	80	°C/W	
Maximum Junction-to-Ambient	Steady State		100	125		
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	34	45		

Notes:

a. Surface mounted on 1" x 1" FR4 board.

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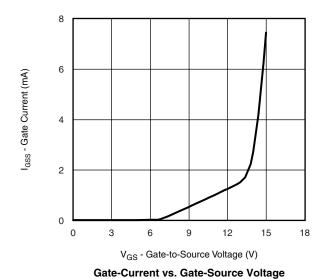
Parameter	Symbol	Test Conditions Min.		Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -100 \mu A$	- 0.45			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			± 1.5	μΑ	
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 10	mA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 16 V, V _{GS} = 0 V			- 1	μΑ	
		$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 85 ^{\circ}\text{C}$			- 5		
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 4.5 V	- 4			Α	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = -2.9 \text{ A}$		0.095	0.115		
		V _{GS} = - 2.5 V, I _D = - 2.4 A		0.125	0.155	Ω	
		V _{GS} = - 1.8 V, I _D = - 1.0 A		0.180	0.220		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 2.9 A		6		S	
Diode Forward Voltage ^a	V_{SD}	I _S = - 1.4 A, V _{GS} = 0 V		- 0.8	- 1.1	V	
Dynamic ^b							
Total Gate Charge	Q_g			5.6	8	nC	
Gate-Source Charge	Q_{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -2.9 \text{ A}$		1.2			
Gate-Drain Charge	Q_{gd}			1.2			
Turn-On Delay Time	t _{d(on)}			0.75	1.1	- μs	
Rise Time	t _r	$V_{DD} = -10 \text{ V}, R_{L} = 10 \Omega$		1.6	2.3		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 1 Å, V_{GEN} = - 4.5 V, R_g = 6 Ω		3.9	5.5		
Fall Time	t _f			3.9	5.5		

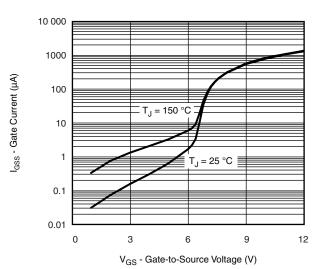
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

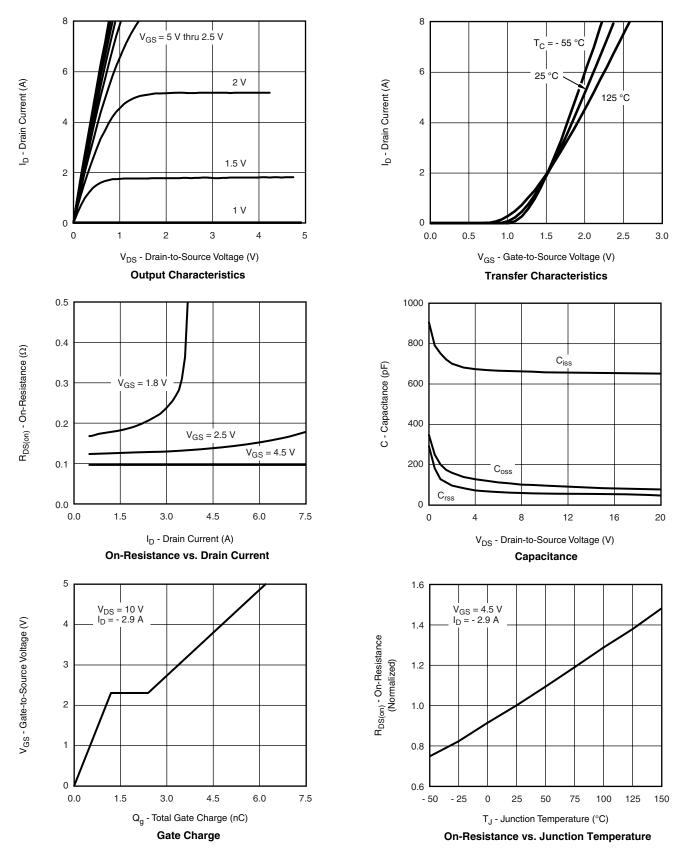




Gate-Current vs. Gate-Source Voltage



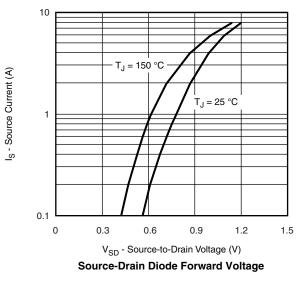
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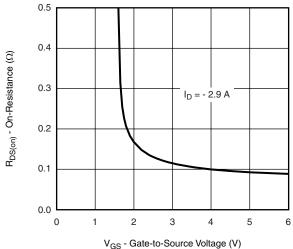


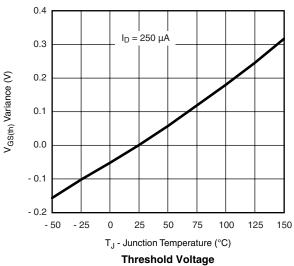
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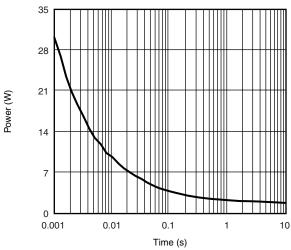
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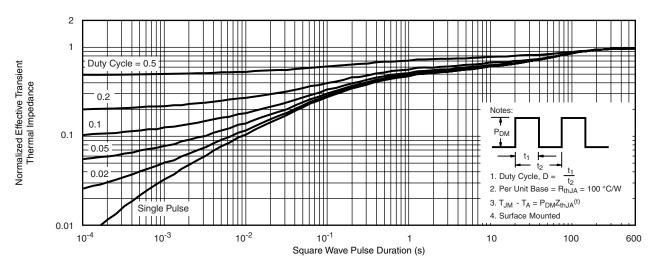




On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient

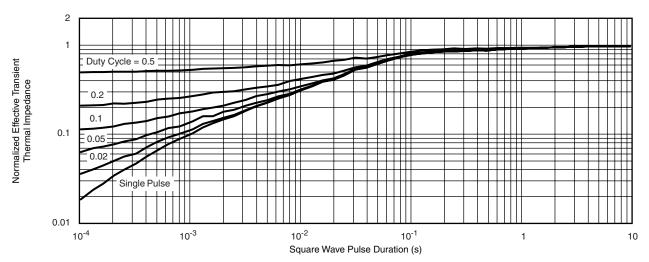


Normalized Thermal Transient Impedance, Junction-to-Ambient





TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

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